

**Supporting information for**

**Internal Defects-Oriented Dissolution: Controllable Evolution to  
Hollow ZSM-5 Nano-Structures**

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**Table S1** Bulk and surface compositions of the samples

Samples	Si/Al ratio		
	XRF(Bulk)	EDX(Bulk)	XPS(Surface)
ZSM	81.8	90.2	16.9
ZSM-T	51.9	38.0	43.4
ZSM-N-D	37.4	25.8	59.3

**Table S2** Assignment and relative intensities of the peaks in the  $^{29}\text{Si}$  MAS NMR spectra of samples.

$\delta/\text{ppm}$	Si site	Relative Peak Area/%		
		ZSM-5-A	ZSM-5-T	ZSM-5-N
~-104	Si(OSi) <sub>3</sub> OH	11.4	7.4	9.1
~-108	Si(OSi) <sub>3</sub> Al	2.6	0.9	2.8
~-111	T <sub>1</sub> Si(OSi) <sub>4</sub>	6.8	10.7	8.4
~-113	T <sub>2</sub> Si(OSi) <sub>4</sub>	31.5	47.4	30.8
~-115	T <sub>3</sub> Si(OSi) <sub>4</sub>	28.5	16.2	38.8
~-116	T <sub>4</sub> Si(OSi) <sub>4</sub>	19.2	17.5	10.2

**Table S3** Notation of the samples and reacting conditions

Samples	Etching Media	Temp./ K	C <sup>a</sup>	LSR <sup>b</sup>	Time/min	Conditions
ZSM	-	453	-	-	1440	c
ZSM-T	TPAOH (a.q.)	443	0.5	7.5	4320	e
ZSM-N-S	NH <sub>3</sub> (a.q.)	353	1	100	480	d
ZSM-N-D	NH <sub>3</sub> (a.q.)	353	1	100	40	e
Silicalite-1	-	453	-	-	4320	c
Silicalite-1-H	NH <sub>3</sub> (a.q.)	353	1	100	40	e

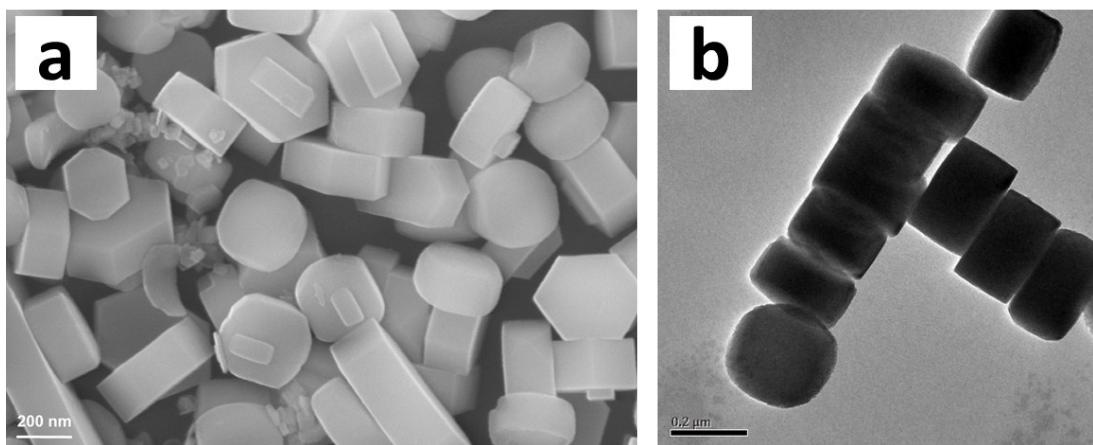
a. Concentrations of the etching media (mol/L).

b. Liquid to solid ratio (mL/g).

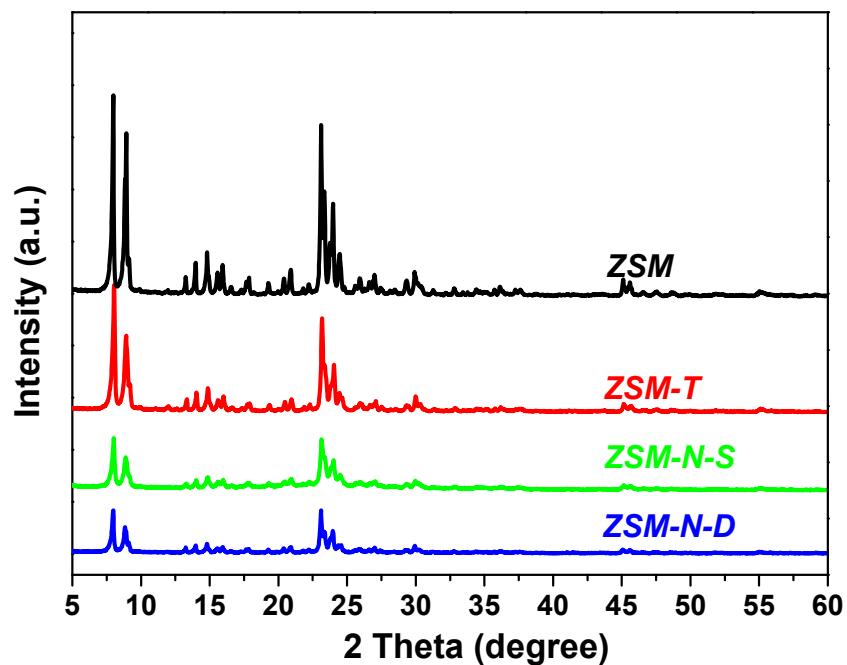
c. Synthesized in sealed autoclaves.

d. Etched under static condition in open reactors.

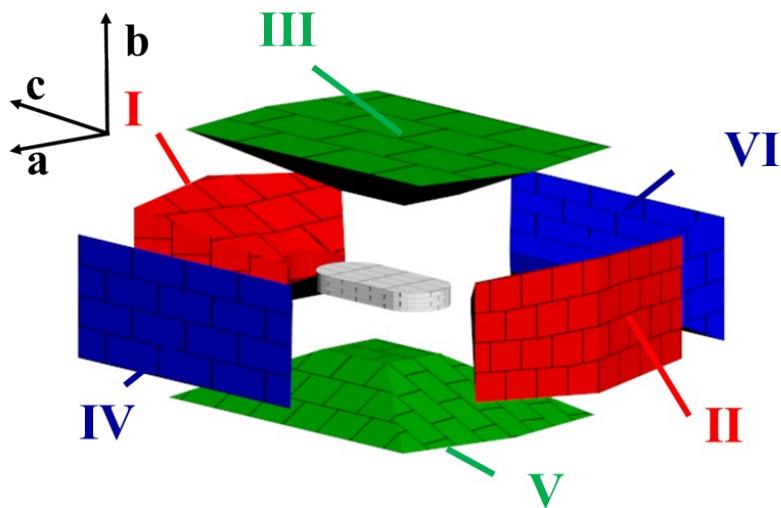
e. Etched under vigorous stirring in open reactors.



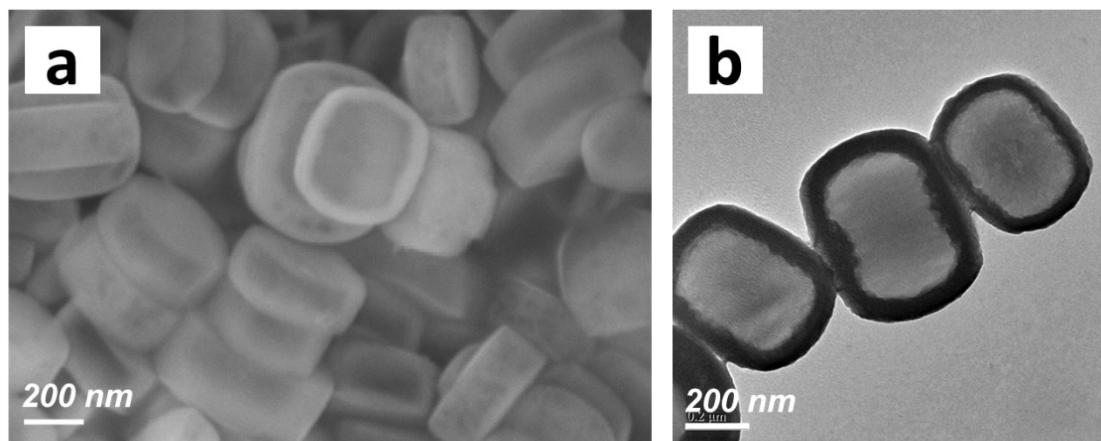
**Fig. S1** SEM (a) and TEM (b) images of pristine ZSM-5 nanocrystal samples.



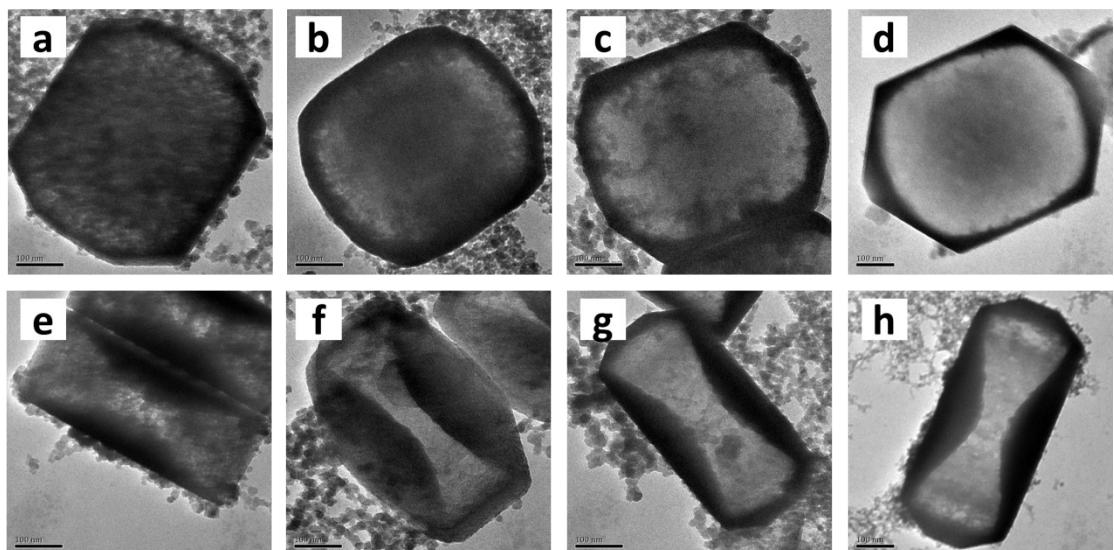
**Fig. S2** XRD patterns of the ZSM-5 precursor (ZSM), TPAOH etched ZSM-5 (ZSM-T), static etched ZSM-5 (ZSM-N-S) by ammonia for 8 h and dynamic etched ZSM-5 (ZSM-N-D) by ammonia under stirred condition for 40 min.



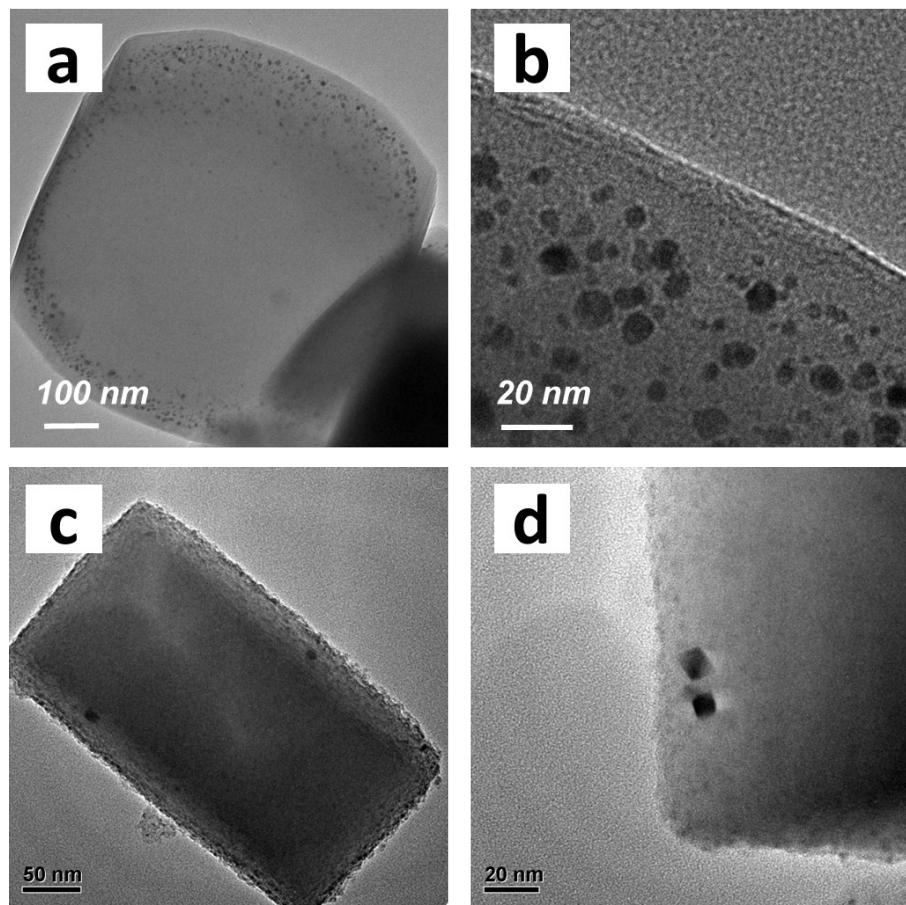
**Fig. S3** Exploded representation of the MFI-type crystals with distinct intergrowth structures and diffusion barriers.<sup>1</sup>



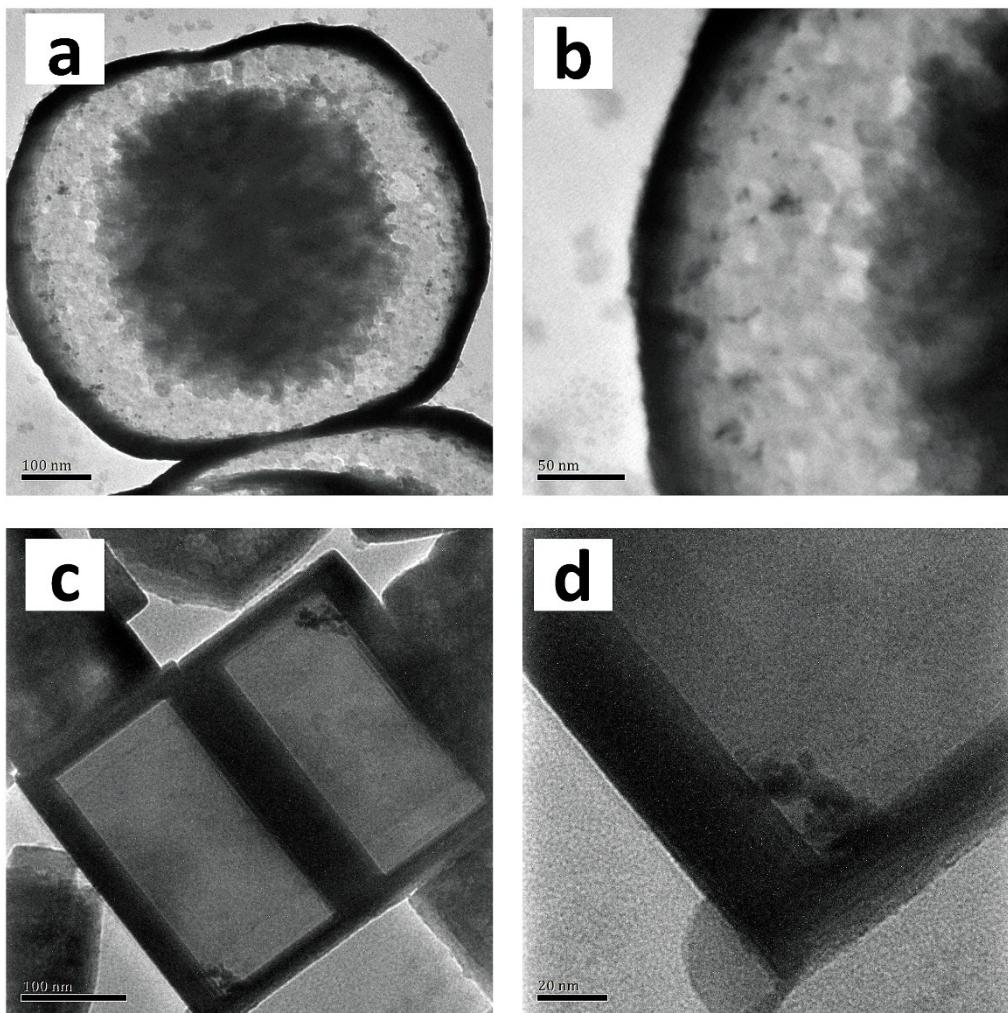
**Fig. S4** SEM(a) and TEM (b)images of hollow ZSM-5 (ZSM-T) nanocrystals etched with TPAOH.



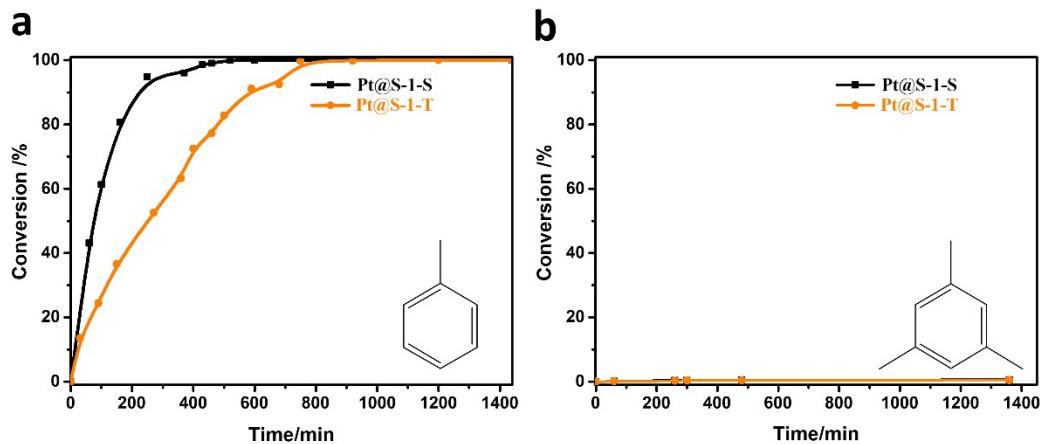
**Fig. S5** TEM images of the evolution process of the hollow silicalite-1 nanocrystals (diameter: 300~500 nm) etched by ammonia under static conditions for (a)(e) 10 min, (b)(f) 20 min, (c)(g) 30 min (d)(h) 40 min.



**Fig. S6** HRTEM images of the Pt@silicalite-1 (a) (b) and Pt/silicalite-1(c) (d) catalysts.



**Fig. S7** TEM images of the Pt@silicalite-1 catalysts etched with TPAOH (a) (b) and Pt@silicalite-1 etched with ammonia under static condition (c) (d).



**Figure S8** Catalytic performance of the hollow Pt@silicalite-1-H catalysts etched with TPAOH (Pt@S-1-T) and Pt@silicalite-1-H etched with ammonia under static conditions (Pt@S-1-S) for toluene (a) and (b) mesitylene hydrogenation.

## References

1. M. B. J. Roeffaers, R. Ameloot, M. Baruah, H. Uji-i, M. Bulut, G. De Cremer, U. Müller, P. A. Jacobs, J. Hofkens, B. F. Sels and D. E. De Vos, *J. Am. Chem. Soc.*, 2008, 130, 5763.